



# TSB94S150S(A)S-255A

10A/150V<sup>(1)</sup>, low VF Schottky barrier with trench MOS structure

## Mechanical Data

Chip Drawing	Item	Information	
	Die Size (A)	2388 μm	94 mil
	Top Metal (B)	2286 μm	90 mil
	Chip Size (C)	2311 μm	91 mil
	Wafer Thickness (D)	255 μm	9.5 mil
	Scribe Line (E/2)	80 μm	3.15 mil
	Wafer Size	6 inch	
	Top Side Metal	AL/Ag	
	Back Side Metal	Ti Ni Ag	
Recommended Storage Environment	Stored in original container, in dry nitrogen, (6 months at an ambient temperature of 23 ±3 °C)		

## Electrical Characteristics (T<sub>J</sub>=25°C, unless otherwise specified)<sup>(2)</sup>

Parameter	Description	Typ.	Max.	Unit	Test Condition
V <sub>BR</sub>	Reverse Breakdown Voltage	70	-	V	I <sub>R</sub> = 100 μA
V <sub>F</sub>	Instantaneous Forward Voltage	0.8	0.88	V	I <sub>F</sub> = 10A <sup>(3)</sup>
I <sub>R</sub>	Reverse Leakage Current	0.5	10	μA	V <sub>R</sub> = 150V
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature	0	Max	°C	